



Form PTO-449

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)

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Applicant

Yukio YAMASAKI et al.

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U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO

OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
NY	1.	Nagahama, S-i., et al. (2000). "High-Power and Long-Lifetime InGaN Multi-Quantum-Well Laser Diodes Grown on Low-Dislocation-Density GaN Substrates," <i>Jpn. J. Appl. Phys.</i> 39:L647-L650.
NY	2.	Tojyo, T. et al. (2002). "High-Power AlGaN Laser Diodes with High Kink Level and Low Relative Intensity Noise," <i>Jpn. J. Appl. Phys.</i> 41:1829-1833.

X

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7/17/06

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.